



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Inventor: Yukihiko INOUE

Group Art Unit: 2811

Appln. No.: 09/768,556

Examiner: S. Gebremariam

Filed: January 25, 2001

For: SEMICONDUCTOR DEVICE

AMENDMENT UNDER 37 CFR § 1.111

Assistant Commissioner of Patents  
Washington, D.C. 20231

Sir:

In response to the Office Action dated January 30, 2003,  
please amend the above-captioned application as follows:

IN THE CLAIMS:

Please amend the claims as follows (Exhibit I contains a  
marked up version):

11. (Twice Amended) A semiconductor device according to  
claim 13, wherein said transistor is a high voltage transistor  
having a source diffusion layer within said source side offset  
diffusion layer region and a drain diffusion layer within said  
drain side offset diffusion layer region and said source side  
offset diffusion layer and said drain side offset diffusion layer  
have impurity concentrations lower than those of said source  
diffusion layer and said drain diffusion layer.

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#16/Dw/attach  
4/30/03

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